Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L10	194992	disposable	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/06 08:01
L11	1038732	(sidewall side adj (wall surface))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/06 08:02
L12	1842845	insulat$4 dielectric	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/06 08:02
L13	383897	spacer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/06 08:02
L14	36353	L11 near3 L12	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/06 08:02
L15	409506	L13 L14	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/06 08:08
L16	405	10 adj 15	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/06 09:26
L17	353592	sin nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/06 08:08
L18	1466248	oxide sio	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/06 08:09
L19	134926	17 with 18	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/06 08:09

L20	88	16 same 19	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/06 08:09
L21	51	16 with 19	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/06 08:10
L22	157759	liner	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/06 08:10
L23	1642	19 with 22	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/06 08:11
L24	3	16 same 23	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/06 08:19
L25	28	16 and 23	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/06 08:19
L26	537	10 adj2 15	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/06 09:26
L27	29	26 and 23	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/06 09:26
L28	1	27 not 25	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/06 09:28
L29	2586	18 near3 22	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/06 09:29

L30	10125	17 near4 15	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/06 09:29
L31	267	29 same 30	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/06 09:29
L32	948931	gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/06 09:29
L33	194	31 same 32	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/06 09:30
L34	4287522	etch$4 remov$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/06 09:31
L35	5130	30 with 34	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/06 09:31
L36	116	33 and 35	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/06 09:46
L37	17856	ldd	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/06 09:46
L38	42	33 and 37	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/06 09:47
L39	77393	p adj (channel (tft fet mosfet type near2 transistor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/06 12:19

L40	95194	n adj (channel (tft fet mosfet type near2 transistor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/06 12:19
L41	53319	L39 with L40	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/06 12:19
L42	3037978	width thickness	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/06 12:21
L43	5669656	greater different smaller larger thinner	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/06 12:21
L44	487881	L42 near3 L43	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/06 12:21
L45	409506	L13 L14	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/06 12:21
L46	4941	L44 near6 L45	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/06 12:22
L47	14	46 same 41	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/06 12:22
L48	198	46 and 41	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/06 12:23
S1	0	10/753914	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/10 11:07

S2	1	09/948877	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/05 10:37
S3	1736	"KONINKLIJKE PHILIPS".as.	USPAT	OR	ON	2003/08/19 13:35
S4	0	10/790420	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/25 12:22
S5	1036127	(sidewall side adj (wall surface))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/05 12:09
S6	93319	n adj (channel (type near2 transistor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/25 12:24
S7	75665	p adj (channel (type near2 transistor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/05 12:04
S8	49068	nmos n adj mos	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/25 12:25
S9	42124	pmos p adj mos	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/25 12:26
S10	128184	S8 S6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/25 12:26
S11	105926	S9 S7	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/25 12:26
S12	76227	S10 with S11	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/25 12:26

S13	970	S5 near6 S10	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/25 12:26
S14	830	S5 near6 S11	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/25 12:26
S15	471	S13 same S14	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/25 12:26
S16	393	S13 with S14	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/25 12:28
S17	3030879	width thickness	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/05 12:06
S18	528677	spacer liner	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/25 12:29
S19	1452481	S5 S18	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/25 12:29
S20	62872	S17 near3 S19	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/25 12:30
S21	139	S20 near9 S10	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/25 12:30
S22	69	S15 and S21	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/25 12:33

S23	3991289	(pressure stress strain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/25 12:33
S24	360848	lattice compressive relaxed strained	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/25 12:34
S25	90560	S23 same S24	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/25 12:34
S26	3	S22 and S25	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/25 12:39
S27	35	S22 and S23	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/25 12:39
S28	13	S22 and S24	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/25 12:39
S29	9	S27 and S28	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/25 12:39
S30	1323201	removing	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/25 12:40
S31	485295	mask	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/25 12:40
S32	891406	(mask$4 reticl$4 resist)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/25 12:40

S33	946114	gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/25 12:41
S34	11725	S30 near3 S19	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/25 12:41
S35	60217	S32 with S33	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/25 12:47
S36	571	S34 with S35	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/25 12:47
S37	22	S15 and S36	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/25 12:47
S38	92	S36.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/25 12:47
S39	22	S15 and S37	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/25 12:48
S40	6	S15 and S38	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/25 12:48
S41	0	10/790420	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/05 13:35
S42	77393	p adj (channel (tft fet mosfet type near2 transistor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/05 12:05

S43	95194	n adj (channel (tft fet mosfet type near2 transistor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/05 12:05
S44	3037978	width thickness	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/05 12:07
S45	5669656	greater different smaller larger thinner	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/05 12:08
S46	487881	S44 near3 S45	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/05 12:09
S47	53319	S42 with S43	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/06 12:19
S48	1038732	(sidewall side adj (wall surface))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/05 12:10
S49	1842845	insulat$4 dielectric	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/05 12:10
S50	383897	spacer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/05 12:10
S51	36353	S48 near3 S49	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/05 12:11
S52	409506	S50 S51	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/06 08:02

S53	4941	S46 near6 S52	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/06 12:21
S54	7	S53 with S47	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/05 12:12
S55	14	S53 same S47	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/05 12:12
S56	32	("5296401").URPN.	USPAT	OR	ON	2005/07/05 12:30
S57	8	("6316302").URPN.	USPAT	OR	ON	2005/07/05 12:56
S58	0	("6551870").URPN.	USPAT	OR	ON	2005/07/05 13:01
S59	27	("4745086" | "4978626" | "4994404" | "5069747" | "5286664" | "5405791" | "5536684" | "5580804" | "5610088" | "5654213" | "5693974" | "5780350" | "5783458" | "5786257" | "5824588" | "5847428" | "5880006" | "5904529" | "5970353" | "6221564" | "6228731" | "6284630" | "6316302" | "6316321" | "6323077" | "6335252" | "6342423").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/07/05 13:01
S60	80	S55 S56 S57 S59	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/05 13:54
S61	26881	soi	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/05 13:35
S62	10	S60 and S61	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/05 13:35
S63	2	10/017237	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/05 16:44
S64	1	("6610565").URPN.	USPAT	OR	ON	2005/07/05 13:55
S65	6	("4722909" | "4818714" | "5015595" | "5045916" | "5229307" | "5930634").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/07/05 13:55

S66	1217	bf2	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/05 16:44
S67	345672	dop$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/05 16:44
S68	137	S66 near9 S67	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/05 17:45
S69	277674	(s?licid$4 silicat$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/05 17:45
S70	2511360	resistance conductivity	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/05 17:46
S71	11704	S69 near5 S70	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/05 17:56
S72	1093	nitride near liner	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/05 17:57
S73	13	S60 and S71	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/05 18:02
S74	1420036	oxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/05 18:02
S75	574	S72 with S74	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/05 18:03

S76	90	S75 with S52	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/05 18:28
S77	69466	dry adj etch$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/05 18:31
S78	2707	S77 with S52	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/05 18:31
S79	12	S78 and S60	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/06 08:00